# **PUB4124** (PU4124), **PUB4424** (PU4424)

## Silicon NPN triple diffusion planar type darlington

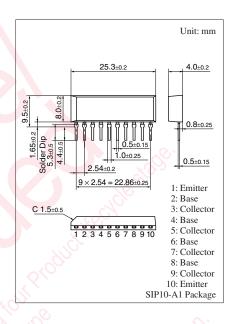
#### For power amplification

#### ■ Features

- Built-in zener diode (60 V) between collector and base
- Small variation in withstand pressure
- Large energy handling capability
- High-speed switching
- PUB4124 (PU4124): NPN 4 elements PUB4424 (PU4424): NPN 2 elements × 2

#### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60±10	V
Collector-emitter voltage (Base open)	$V_{CEO}$	60±10	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_{C}$	4	A
Peak collector current	$I_{CP}$	8	A
Collector power dissipation	$P_{C}$	15	W
$T_a = 25$ °C		3.5	
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C O



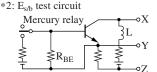
### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\text{CEO}}$ $I_{\text{C}} = 5 \text{ mA}, I_{\text{B}} = 0$		0. (0	70	V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_{E} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 5 \text{ V}, I_C = 0$	2	69	2	mA
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 0.5 \text{ A}$	1 000			_
	h <sub>FE2</sub> *1	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ A}$	1 000		10 000	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 3 A, I <sub>B</sub> = 12 mA			2.0	V
		$I_C = 5 \text{ A}, I_B = 20 \text{ mA}$			4.0	
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 12 \text{ mA}$			2.5	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t <sub>on</sub>	$I_C = 3 \text{ A}$		0.3		μs
Storage time	t <sub>stg</sub>	$I_{B1} = 12 \text{ mA}, I_{B2} = -12 \text{ mA}$		3.0		μs
Fall time	$t_{\rm f}$	$V_{CC} = 50 \text{ V}$		1.0		μs
Energy handling capability *2	E <sub>s/b</sub>	$I_C = 1 \text{ A, L} = 100 \text{ mH, R}_{BE} = 100 \Omega$	50			mJ

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*1: Rank classification

Rank	Free	Р	Q	
$h_{ m FE}$	1000 to 10000	2000 to 10000	1000 to 5000	

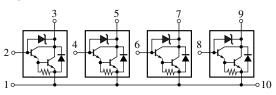


Note) The part numbers in the parenthesis show conventional part number.

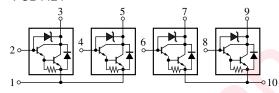
## **Panasonic**

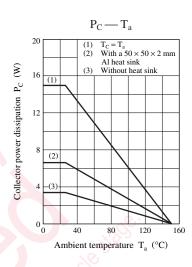
#### ■ Internal Connection

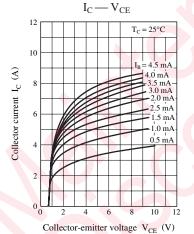
#### • PUB4124

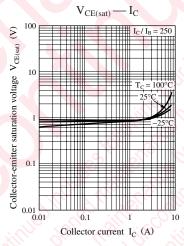


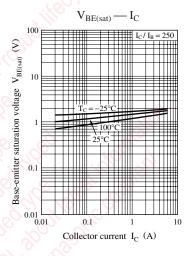
#### • PUB4424

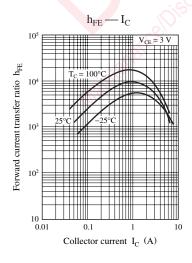


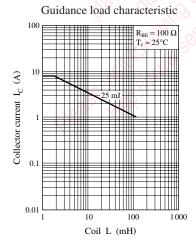


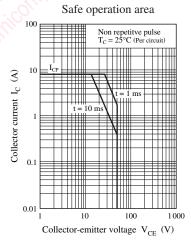












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